

ABSTRACT

A field effect transistor and method of fabricating the field effect transistor. The field effect transistor, including: a gate electrode formed on a top surface of a gate dielectric layer, the gate dielectric layer on a top surface of a single-crystal silicon channel region, the single-crystal silicon channel region on a top surface of a Ge including layer, the Ge including layer on a top surface of a single-crystal silicon substrate, the Ge including layer between a first dielectric layer and a second dielectric layer on the top surface of the single-crystal silicon substrate.